IN THE SPECIFICATION:

Amend the specification as follows:

Paragraph beginning at page 1, line 5 has been amended as follows:

A2

The present invention relates to high frequency semiconductor devices, and in particular, to a multilayer wiring structure for monolithic microwave integrated circuit (MMIC) for use in the gigahertz ~~frequency~~ or higher frequency spectrum.

Paragraph beginning at page 2, line 6 has been amended as follows:

A3

Specifically, Fig. 1B shows a three-layer wiring structure in which wiring layers 51, 53, and 55 are alternatively stacked, with insulating interlayers 50, 52, and 54 provided therebetween. Each of the wiring layers 51, 53, and 55 combines with the ground plate 5 to form a transmission line. The connection between two wiring layers and the connection between each wiring layer and each device are established by ~~throughholes~~ through-holes (not shown), as required.

Paragraph beginning at page 2, line 23 has been amended as follows:

A4

When two wiring layers cross each other, as described above, the transmission characteristics deteriorate, for example, ~~as an occurence of~~ signal leakage may occur, because signals transmitted by transmission lines made of wiring layers mutually interfere where they cross one another. To prevent the deterioration, a method is employed in which, by forming an

insulating interlayer between upper and lower wiring layers which cross each other, and providing a separation plate on the insulating interlayer, the wiring layers are electrically separated.

Paragraph beginning at page 5, line 3 has been amended as follows:

To this end, according to the present invention, the above object is achieved through provision of a multilayered wiring structure for high frequency semiconductor devices which includes a semiconductor substrate, a ground plate which is formed above said semiconductor substrate and which have a potential fixed at the ground potential , a plurality of wiring layers each of which is alternately stacked with insulating interlayer above the semiconductor substrate and combines with the ground plate to form transmission ~~line~~ lines, and at least one separation electrode which is selectively provided on the additional insulating interlayer and which has a potential fixed at the ground potential. The multilayered wiring structure has at least one crossing portion where the wiring layers mutually cross, with insulating interlayers provided therebetween.

Paragraph beginning at page 5, line 18 has been amended as follows:

Preferably, the ~~size~~ length and width of dimensions of at least one separation electrode is sufficiently smaller than the length of each of the transmission lines above the semiconductor substrate so as to not significantly interfere with transmission line characteristics of the wiring layers.

Paragraph beginning at page 5, line 21 has been amended as follows:

A7 Each of the crossing portions may have ~~the~~ an individual separation electrode.

Paragraph beginning at page 6, line 6 has been amended as follows:

A8 The separation electrodes may be provided on different insulating interlayers, and may be electrically and directly interconnected by at least one ~~throughhole~~ through-holes.

Paragraph beginning at page 6, line 9 has been amended as follows:

A9 A single separation electrode may be ~~in common~~ provided for all of the crossing portions.

Paragraph beginning at page 6, line 11 has been amended as follows:

A10 The crossing portions may be positioned at different levels, and the separation electrodes may be provided on those of the insulating interlayers which are provided ~~in common in~~ for all of the crossing portions.

Paragraph beginning at page 6, line 15 has been amended as follows:

A11 The crossing portions may be positioned at different levels, and the single separation electrode may be provided on one of the insulating interlayers which is provided ~~in common in~~ for all of the crossing portions.

Paragraph beginning at page 6, line 19 has been amended as follows:

In the present invention, crossing wiring layers are electrically separated by the separation electrode which is selectively provided in a crossing portion. Thus, they cannot mutually interfere. Above a semiconductor substrate, in portions other than the crossing portion, the wiring layers combine with a ground plate to form ordinary transmission lines, so that transmission loss is not increased, compared with a case in which the wiring layers do not cross. Therefore, by sufficiently reducing one of the ~~size~~ length and width of the separation electrode to be less than the length of each transmission line, the total transmission loss of all the transmission lines can be reduced ~~than~~ compared to the cases in the related art.

A12

Paragraph beginning at page 11, line 17 has been amended as follows:

Fig. 4 shows a case in which the wiring layers 14, 16, 20, and 22 cross above a GaAs substrate 1 in a plurality of portions, with the insulating interlayers 13, 15, 17, 19, and 21 provided therebetween. In each of the crossing portions 100, each separation electrode 18 is provided. By electrically interconnecting these separation electrodes 18, and fixing their potential to a predetermined potential, for example, the ground potential, the transmission characteristics can be further stabilized.

A13

Paragraph beginning at page 12, line 1 has been amended as follows:

Fig. 5 shows a case in which a plurality of crossing portions 100 are divided into a plurality of groups which are close to each other above a GaAs substrate 1. In this case, a common separation electrode is provided for wiring layers belonging to a single group, and other common separation

A14

electrodes are provided for pluralities of wiring layers which belong to other groups. As described above, by using wiring layer 23 to interconnect the separation electrodes 18, their potential may be fixed to the ground potential.

Paragraph beginning at page 12, line 10 has been amended as follows:

In addition, as shown in Fig. 6, in a case in which a plurality of crossing portions 100 are formed on different insulating interlayers 13, 15, 17, 19, and 21, respectively, each separation electrode 18 is provided on each insulating interlayer, and the separation electrodes 18 are electrically connected by ~~throughholes~~ through-holes which penetrate the insulating interlayers 17 and 19.